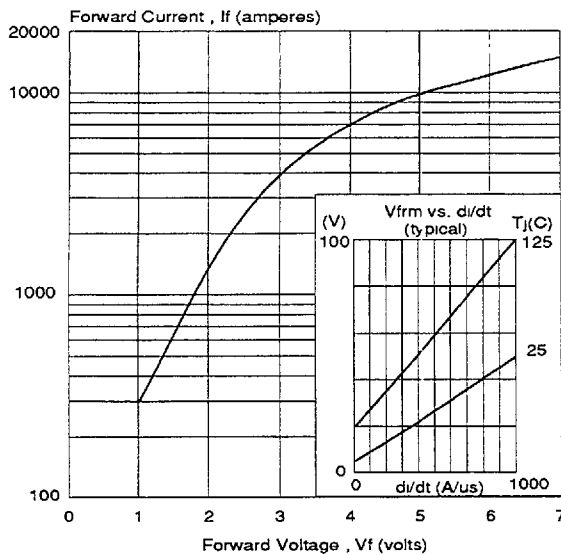


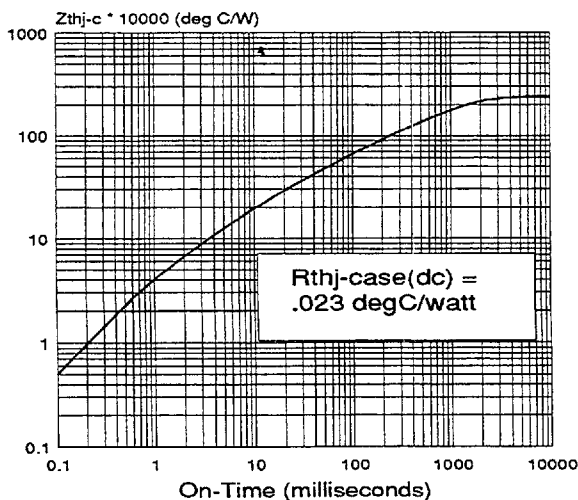
The A796 fast recovery diode is designed as a parallel mate for GTO's used in voltage fed inverter circuits normally requiring the bypass function. Its relatively low recovery current and charge in combination with low thermal resistance offer a new advantage for optimizing other circuit components. It is manufactured by the proven multi-diffusion process with 53 mm diameter silicon and is supplied in a disc-type package ready to mount using commercially available heat dissipators and clamping hardware.

FORWARD CHARACTERISTIC
Process Maximum @ T_J=125°C



810 328/81

THERMAL IMPEDANCE vs. ON-TIME

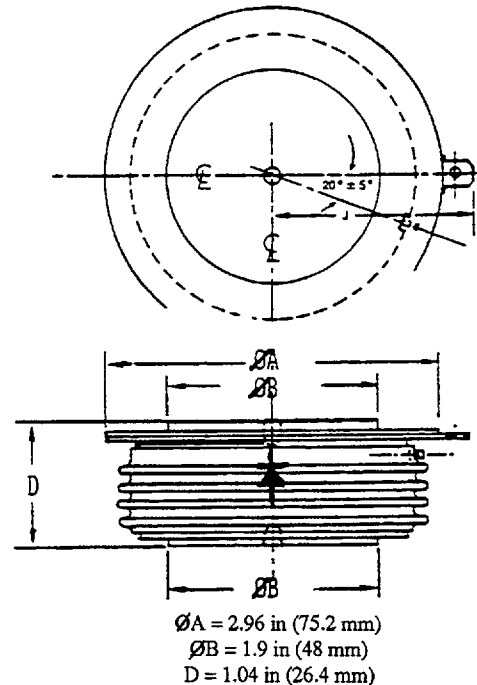


MAXIMUM RATINGS & PARAMETERS

Maximum repetitive peak reverse voltage	V _{RRM}	T _J = -40 to +125°C	to 2500	V
Maximum forward average & RMS current ratings	I _{F(AV)} I _{RMS}	T _{case} 70°C	925 1450	A
Maximum reverse leakage current	I _{RRM}		75	ma
Forward voltage drop	V _{FM}	I _F =5000A t _F =8.3ms T _J =125°C	3.35	V
Maximum peak recovery current	I _{RR}	@ 10 A/us @ 100 A/us	45 280	A
Maximum recovery charge	Q _{RR}	@ 10 A/us @ 100A/us	200 800	uC
Typical recovery time and snap factor	t _{RR}		4 0.5	us

*(tested with 1uF, 4 ohm snubber)

MECHANICAL OUTLINE



CLAMPING FORCE REQUIRED
5000 - 6000 lb / 22.4 - 26.7 kN

SILICON POWER CORPORATION
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date:3/29/91

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